TO-251 P MOS P-CHANNEL MOSFET in a TO-251 Plastic Package.

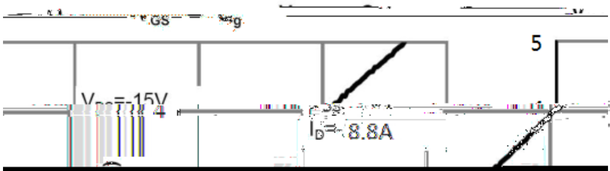
$R_{DS(on)}$ C_{rss}

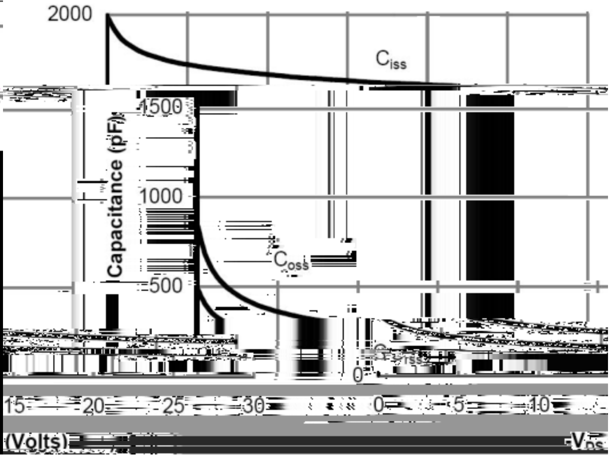
Low $R_{DS(on)}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Drain Current	I_D(Tc=25)	-20	A
Drain Current - Pulsed	I_{DM}	-50	A
Gate-Source Voltage	V_{GS}	±20	V
Single Pulsed Avalanche Energy	E_{AS}	50	mJ
Power Dissipation	P_D(Tc=25)	30	W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

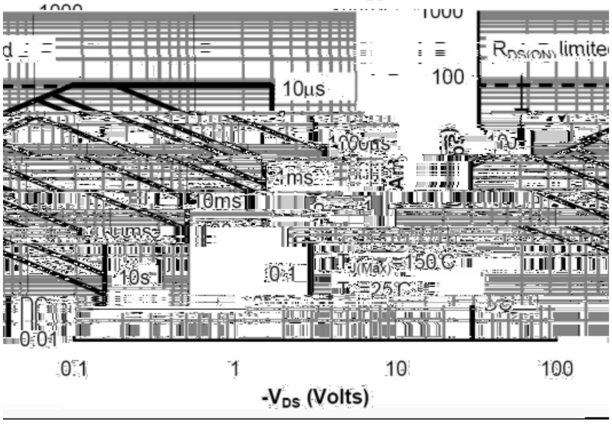
Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V	I_D=-250μA	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V	V_{GS}=0V			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V	V_{DS}=0V			±0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}	I_D=-250μA	-1		-2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)1}$	V_{GS}=-10V	I_D=-8.8A		18	23	mΩ
	$R_{DS(on)2}$	V_{GS}=-4.5V	I_D=-6.7A		27	35	mΩ
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V	I_S=-2.1A		-0.73	-1.2	V
Input Capacitance	C_{iss}	V_{DS}=-15V f=1.0MHz	V_{GS}=0V		1604		pF
Output Capacitance	C_{oss}				408		
Reverse Transfer Capacitance	C_{rss}				202		
Total Gate Charge	Q_g	V_{DS}=-15V V_{GS}=-5V	I_D=-8.8A		17ref386.yR337.9.47998 1		

/ Electrical Characteristic Curve

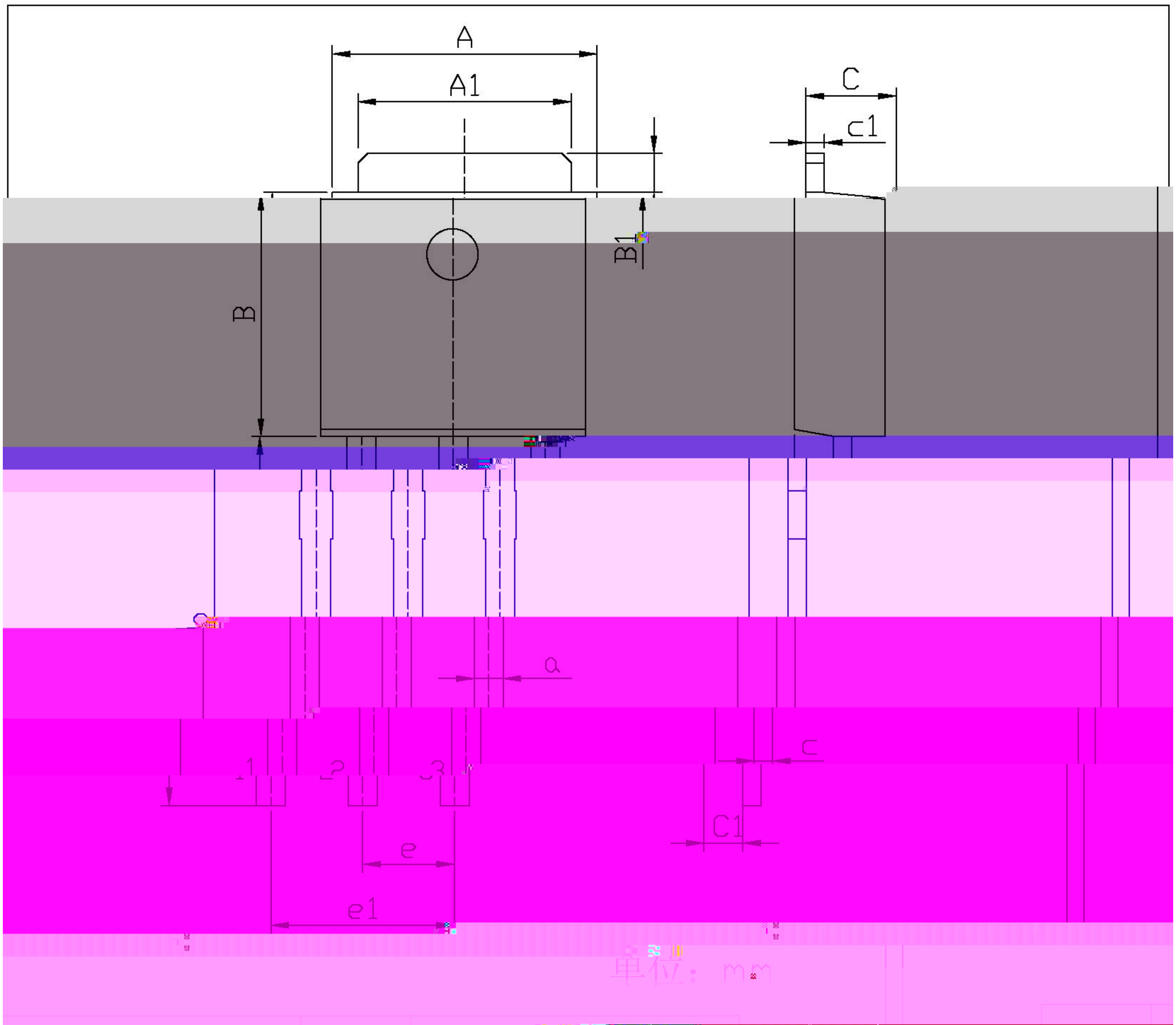




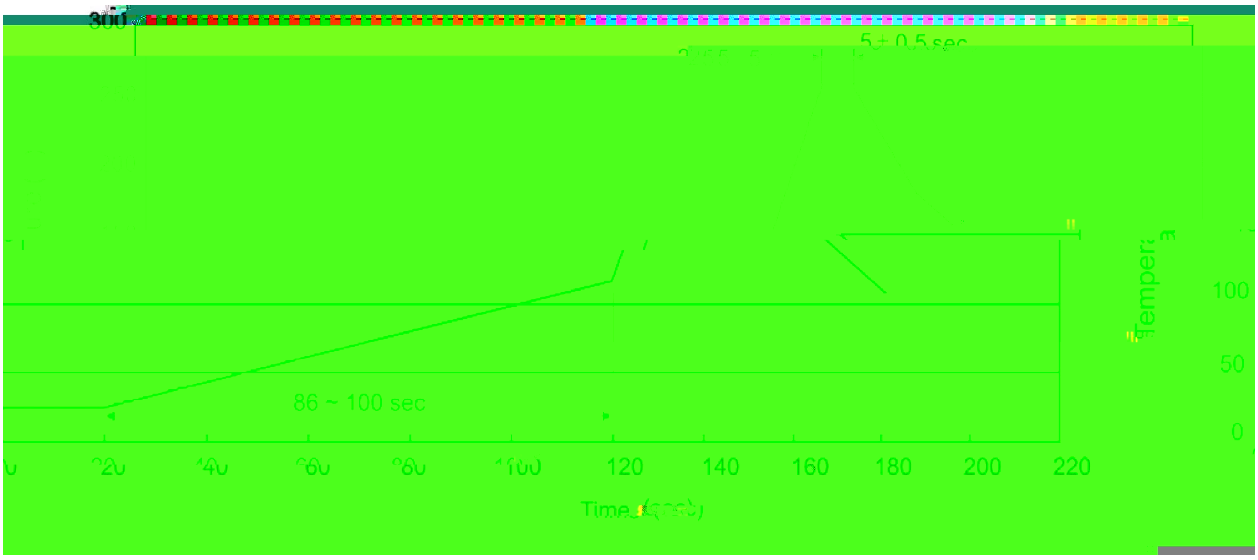
$-I_D$ — $-V_{DS}$



/ Package Dimensions



(   ) / Temperature Profile for Dip Soldering(Pb-Free)



Note:

1 25 150 60 90sec;
2 255±5 5±0.5sec;
3 2 10 /sec.

1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit mm^3)

/ TUBE

Package Type	Units					Dimension		(unit mm^3)

/ Notices